

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

RFL1N12, RFL1N15

1A, 120V and 150V, 1.9 Ohm,
N-Channel Power MOSFETs

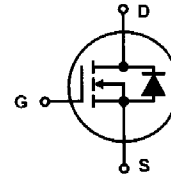
Features

- 1A, 120V and 150V
- $r_{DS(ON)} = 1.9\Omega$
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

Description

These are N-Channel enhancement mode silicon gate power field effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Symbol

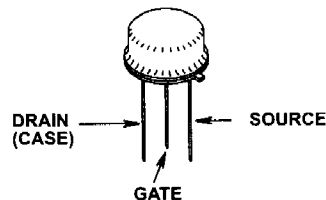


Ordering Information

PART NUMBER	PACKAGE	BRAND
RFL1N12	TO-205AF	RFL1N12
RFL1N15	TO-205AF	RFL1N15

Packaging

JEDEC TO-205AF



Quality Semi-Conductors

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFL1N12	RFL1N15	UNITS	
Drain to Source Voltage (Note 1)	V_{DSS}	120	150	V
Drain to Gate Voltage ($R_{GS} = 1M\Omega$) (Note 1)	V_{DGR}	120	150	V
Continuous Drain Current	I_D	1	1	A
Pulsed Drain Current	I_{DM}	5	5	A
Gate to Source Voltage	V_{GS}	± 20	± 20	V
Maximum Power Dissipation	P_D	8.33	8.33	W
Linear Derating Factor		0.0667	0.0667	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering				
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage RFL1N12	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	120	-	-	V
			RFL1N15	150	-	-
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$, (Figure 8)	2	-	4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, T_C = 25^\circ\text{C}$	-	-	1	μA
			$T_C = 125^\circ\text{C}$	-	-	25
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	± 100	nA
Drain to Source On Voltage (Note 2)	$V_{DS(ON)}$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$	-	-	1.9	V
			$I_D = 2\text{A}, V_{GS} = 10\text{V}$	-	-	6.3
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$, (Figures 6, 7)	-	-	1.9	Ω
Forward Transconductance (Note 2)	g_{fs}	$I_D = 1\text{A}, V_{DS} = 10\text{V}$, (Figure 10)	400	-	-	S
Turn-On Delay Time	$t_{d(ON)}$	$I_D = 1\text{A}, V_{DD} = 75\text{V}, R_{GS} = 50\Omega$ $V_{GS} = 10\text{V}$, (Figures 11, 12, 13)	-	17	25	ns
Rise Time	t_r		-	30	45	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	30	45	ns
Fall Time	t_f		-	30	50	ns
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$, (Figure 9)	-	-	200	pF
Output Capacitance	C_{OSS}		-	-	80	pF
Reverse Transfer Capacitance	C_{RSS}		-	-	25	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	15	$^\circ\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	$I_{SD} = 1\text{A}$	-	-	1.4	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 1\text{A}, dI_{SD}/dt = 50\text{A}/\mu\text{s}$	-	150	-	ns